

Docket No.: M4065.0536/P536-B  
(PATENT)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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In re Patent Application of:  
Hongmei Wang et al.

Application No.: NOT YET ASSIGNED

Art Unit: N/A

Filed: January 6, 2004

Examiner: Not Yet Assigned

For: FULLY-DEPLETED (FD) (SOI) MOSFET  
ACCESS TRANSISTOR AND METHOD OF  
FABRICATION

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**FIRST PRELIMINARY AMENDMENT**

MS Non-Fee Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

**INTRODUCTORY COMMENTS**

Prior to examination on the merits, please amend the above-identified U.S. patent application as follows:

**Amendments to the Specification** begin on page 2 of this paper.

**Amendments to the Claims** are reflected in the listing of claims which begins on page 3 of this paper.

**Remarks/Arguments** begin on page 5 of this paper.